

WHAT IS CLAIMED IS:

1. An electrostatic discharge (ESD) protection device, comprising:
 - a semiconductor bulk of a first conductivity type;
 - a first doped region of a second conductivity type formed in said semiconductor bulk;
 - a second doped region of a second conductivity type formed in said semiconductor bulk;
 - a channel region formed between said first doped region and said second doped region;
- 10 a first gate segment formed over a first part of said channel region;
 - a first field-oxide segment formed over a third part of said channel region; wherein
 - a first part of said first gate segment overlaps said first field-oxide segment.
- 15 2. A device according to Claim 1, wherein said first part is a first end.
3. A device according to Claim 1, wherein said first and third parts form a first continuous portion of said channel.
4. A device according to claim 1, wherein said first gate segment and said first field-oxide segment are substantially collinear.
- 20 5. A device according to claim 1, wherein said first gate segment comprises a polysilicon element over an oxide layer.
6. A device according to claim 1, further comprising a plurality of islands formed over said bulk and being enclosed by said first doped region.
- 25 7. A device according to claim 6, wherein said plurality of islands comprises a first and second arrays of islands; said first array of islands comprises polysilicon-over-oxide islands; and said second array of

islands comprises field-oxide islands.

8. A device according to claim 7, wherein said first array of islands is closer to said channel region than said second array of islands.

9. A device according to claim 1, further comprising a second gate segment formed over a second part of said channel region; and a first part of said second gate segment overlaps said first field-oxide segment.

10. A device according to Claim 9, wherein said first part of said second gate segment is a first end of said second gate segment.

11. A device according to claim 1, wherein said second and third parts form a second continuous portion of said channel.

12. A device according to claim 1, wherein said first doped region couples to a pad.

13. A device according to claim 1, wherein said second doped region couples to a power bus.

- 15 14. An electrostatic discharge (ESD) protection device, comprising:
- a semiconductor bulk of a first conductivity type;
 - a first doped region of a second conductivity type formed in said semiconductor bulk;
 - a second doped region of a second conductivity type formed in said semiconductor bulk;
 - a channel region formed between said first and said second doped regions;
 - said channel region comprising a split-channel region and a non-split-channel region;
 - 20 said split-channel region including a first and a second sub-channel regions spaced apart from each other; wherein said first sub-channel region being adjacent to said first doped region and said second sub-

channel region being adjacent to said second doped region;
a first gate segment formed over said first sub-channel region;
a second gate segment formed over said second sub-channel region;
a first field-oxide segment formed over said non-split-channel
region; and said first and said second gate segments form a stack-gate
structure.

- 5 15. A device according to claim 14, wherein said first and said second
gate segments are substantially parallel to each other.
- 10 16. A device according to claim 14, wherein said first gate segment,
said second gate segment and said first field-oxide segment are
substantially parallel to each other.
- 15 17. A device according to claim 14, wherein said split channel region is
connected to said non-split channel region to form a continuous channel
region.
- 20 18. A device according to claim 14, wherein said first gate segment
comprises a polysilicon element over an oxide layer.
- 25 19. A device according to claim 14, wherein said second gate segment
comprises a polysilicon element over an oxide layer.
- 20 20. A device according to claim 14, wherein said first gate segment
have a first part overlapping a field-oxide extension segment; and said
second gate segment have a second part overlapping said field-oxide
extension segment.
21. A device according to Claim 20, wherein said first part is a first end;
and said second part is a second end.
- 25 22. A device according to claim 14, further comprising a plurality of
islands formed over said bulk and being enclosed by said first doped
region.

23. A device according to claim 22, wherein said plurality of islands comprises a plurality arrays of islands.

24. A device according to claim 14, wherein said first doped region coupling to a pad.

5 25. A device according to claim 14, wherein said second doped region coupling to a power bus.

26. An electrostatic discharge (ESD) protection device, comprising:

 a semiconductor bulk of a first conductivity type;

 a first doped region of a second conductivity type formed in said
10 semiconductor bulk;

 a second doped region of a second conductivity type formed in said
 semiconductor bulk;

 a channel region formed between said first and said second doped
 regions;

15 a first and a second arrays of islands formed over said bulk and
 being enclosed by said first doped region; wherein

 said first array of islands comprising polysilicon-over-oxide islands;

 said second array of islands comprising field-oxide islands; and

 said first array of islands being closer to said channel region than

20 said second array of islands.